



NPN POWER DARLINGTON TRANSISTOR ARRAY

D76A5D

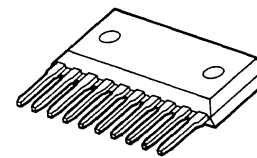
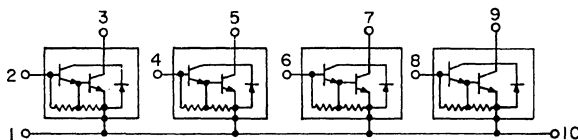
**100 VOLTS
5 AMP, 4 WATTS**

Designed for high power switching applications, hammer drive, pulse motor drive and inductive load drive applications.

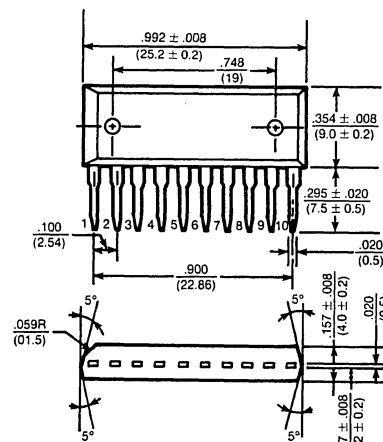
Features:

- High reliability small-sized available (4 in 1)
- Epoxy single-inline package (10 pin)
- High collector power dissipation: $P_D = 4W @ T_A = 25^\circ C$ (Four device action)
- High collector current: $I_C = 5A$ (Max.)
- High DC current gain:
 $h_{FE} = 2000$ (Min.) @ $V_{CE} = 3V, I_C = 3A$

ARRAY CONFIGURATION



CASE STYLE SIP-10 PIN
DIMENSIONS ARE IN INCHES AND (MILLIMETERS)



maximum ratings ($T_A = 25^\circ C$) (unless otherwise specified)

RATING	SYMBOL	D76A5D	UNITS
Collector-Emitter Voltage	V_{CEO}	100	Volts
Collector-Base Voltage	V_{CBO}	100	Volts
Emitter Base Voltage	V_{EBO}	5	Volts
Collector Current — Continuous	I_C	5	A
Peak	I_{CM}	8	
Base Current — Continuous	I_B	0.1	A
Collector Power Dissipation (One Device Action, $T_A = 25^\circ C$)	P_D	2.0	Watts
Collector Power Dissipation (Four Device Action, $T_A = 25^\circ C$)	P_D	4.0	Watts
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

thermal characteristics

Thermal Resistance, Junction to Ambient (Four Device Action)	$\Sigma R_{\theta JA}$	31.3	$^\circ C/W$
Maximum Lead Temperature for Soldering Purpose: 1/8" from Case for 5 Seconds	T_L	260	$^\circ C$

electrical characteristics ($T_A = 25^\circ\text{C}$) (unless otherwise specified)

CHARACTERISTIC	SYMBOL	MIN	TYP	MAX	UNIT
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off characteristics

Collector-Emitter Breakdown Voltage ($I_C = 30\text{mA}$, $I_B = 0$)	$V_{BR(CEO)}$	100	—	—	Volts
Collector Cutoff Current ($V_{CE} = 50\text{V}$, $I_B = 0$)	I_{CEO}	—	—	0.5	mA
Collector Cutoff Current ($V_{CB} = 100\text{V}$, $I_E = 0$)	I_{CBO}	—	—	200	μA
Emitter Cutoff Current ($V_{EB} = 5\text{V}$, $I_C = 0$)	I_{EBO}	—	—	2	mA

on characteristics

DC Current Gain ($I_C = .5\text{A}$, $V_{CE} = 3\text{V}$) ($I_C = 3\text{a}$, $V_{CE} = 3\text{V}$)	h_{FE}	1000 1000	— —	— —	—
Collector-Emitter Saturation Voltage ($I_C = 3\text{A}$, $I_B = 12\text{mA}$) ($I_C = 5\text{A}$, $I_B = 20\text{mA}$)	$V_{CE(sat)}$	— —	— —	2 4	Volts
Base-Emitter Voltage ($I_C = 3\text{V}$, $I_B = 3\text{A}$)	$V_{BE(on)}$	—	—	2.5	Volts

switching characteristics

Turn-on Time	$I_C = 3\text{A}$, $I_{B1} = -I_{B2} = 12\text{mA}$ $V_{BE(off)} = -5\text{V}$, $R_L = 10\Omega$	t_{on}	—	1.5	—	μs
Fall Time		t_f	—	8.5	—	

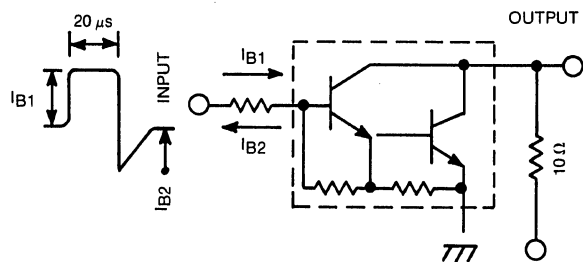


FIG. 1 SWITCHING TIME TEST CIRCUIT